



Docket No.: R2180.0190/P190  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Takaaki Negoro et al.

Application No.: 10/780,699

Confirmation No.: 2014

Filed: February 19, 2004

Art Unit: 2814

For: Metal oxide silicon transistor and semiconductor  
apparatus having high lambda and beta  
performances

Examiner: P. X. Cao

**AMENDMENT AFTER FINAL ACTION UNDER 37 C.F.R. 1.116**

MS AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

In response to the Office Action dated January 4, 2007, finally rejecting claim 1, please amend the above-identified U.S. patent application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 4 of this paper.